

Sat-Pack IGBT

Isolated Base, Dual IGBT Module with Fast Recovery Diode

Part Number FLH001C1S

Features

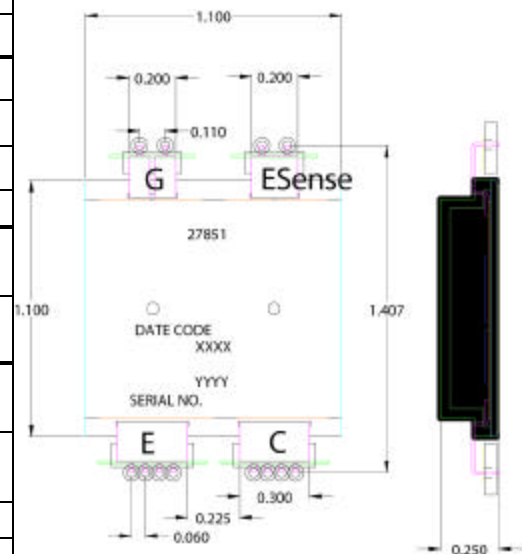
- High power isolated from low power
- Compact design
- Easy to parallel for higher power modules
- Easy Bus Bar Design
- Excellent Thermal management
- Customizable for your die selection

Applications

- Power Factor Correction circuits
- Full bridge topologies
- Half bridge topologies
- Push-Pull Circuits
- Uninterruptible power supplies
- Zero voltage and Zero current switching circuits

Electrical Specifications

PARAMETER	CONDITIONS	VALUES	UNITS
V_{CES}	IGBT + DIODE	600	V_{pk}
I_C	IGBT	150	A_{pk}
I_F	DIODE	150	A_{pk}
T_j	IGBT + DIODE	150	C
GATE DRIVE			
$f_s^{(1)}$	SWITCHING FREQUENCY	5 TO 10	KHz
I_{GES}	GATE / EMITTER SHORTED	< 250	nA
$V_{GE(th)}$	GATE / COLLECTOR SHORTED	4.5	V
THERMAL RESISTANCE	IGBT closest to diode	0.456	$^{\circ}C/Watt$
	IGBT farthest from diode	0.357	$^{\circ}C/Watt$
	Diode	0.850	$^{\circ}C/Watt$



1. Switching frequency can be increased to 20 kHz with decrease in output power.
2. Product is an isolated base design for direct mounting to the heat sink to facilitate maximum performance and flexibility of design and assembly.
3. Thermal resistance numbers are referenced to the average temperature at the bottom surface of the substrate (from FEA model at 55 KW and 200 Volts) and assume a $\sim 150^{\circ}C$ die junction temperature.
4. *Preliminary Data*